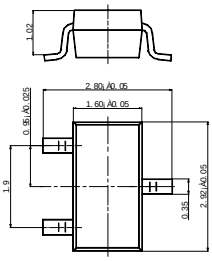
JIANGSU CHANGJIANG ELECTRONICS TECHNOLOGY CO., LTD

SOT-23-3L Plastic-Encapsulate Transistors

2SC3052 TRANSISTOR (NPN)

SOT-23-3L

1. BASE
2. EMITTER
3. COLLECTOR



FEATURES

Power dissipation

P_{CM}: 0.15 W (Tamb=25℃)

Collector current

I_{CM}: 0.2 A

Collector-base voltage

$V_{(BR)CBO}$: 50 V

Operating and storage junction temperature range

T_J, T_{stg}: -55℃ to +150℃

ELECTRICAL CHARACTERISTICS (Tamb=25℃ unless otherwise specified)

Parameter	Symbol	Test conditions	MIN	TYP	MAX	UNIT
Collector-base breakdown voltage	$V_{(BR)CBO}$	Ic=100μA, I_E=0	50			V
Collector-emitter breakdown voltage	$V_{(BR)CEO}$	Ic= 100μA, I_B=0	50			V
Emitter-base breakdown voltage	$V_{(BR)EBO}$	I_E=100μA, I_C=0	6			V
Collector cut-off current	I_{CBO}	V_{CB}=50 V , I_E=0			0.1	μA
Emitter cut-off current	I_{EBO}	V_{EB}= 6V , I_C=0			0.1	μA
DC current gain	$h_{FE(1)}$	V_{CE}=6V, I_C=1mA	150		800	
	$h_{FE(2)}$	V_{CE}=6V, I_C=0.1mA	50			
Collector-emitter saturation voltage	$V_{CE(sat)}$	I_C=100 mA, I_B=10mA			0.3	V
Base-emitter saturation voltage	$V_{BE(sat)}$	I_C=100mA, I_B=10mA			1	V
Transition frequency	f_T	V_{CE}=6V, I_C= 10mA	180			MHz

CLASSIFICATION OF $h_{FE(1)}$

Marking	LE	LF	LG
Range	150-300	250-500	400-800